Unitized Semiconductor Devices - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-106-4654

Inclosure Material:	
Plastic	
Overall Length:	
0.785 inches	
Overall Height:	
0.200 inches	
Overall Width:	
0.375 inches	
Component Name A	And Quantity:
4 transistor	
Mounting Method:	
Press fit	
Features Provided:	
Burn in and hermetic	ally sealed case
Semiconductor Mat	erial:
Silicon all transistor	
Voltage Rating In V	olts Per Characteristic:
60.0 collector to bas	e voltage/static/emitter open all transistor and 40.0 collector to emitter voltage/static/base open all transistor and 5.0
emitter to base voltag	ge, instantaneous all transistor
Current Rating Per	Characteristic:
500.00 milliamperes	source cutoff current all transistor
Power Rating Per C	haracteristic:
1900.0 milliwatts sma	all-signal input power, common-collector preset all transistor
Maximum Operating	g Tempurature Per Measurement Point:
200.0 degrees celsiu	s junction
Special Features:	
All transistor junction	pattern arrangement: npn
Terminal Type And	Quantity:
12 ribbon	
Shelf Life:	
N/a	
Unit Of Measure:	
 Demilitarization:	
No	
Fiig:	
A110a0	